4.75V to 18V Input, 3.0-A Synchronous Step-Down Converter with +/-1.5% High Accuracy

Features

- 3.0-A Output Current
- High Efficient Integrated FETs Optimized for portable application:
  85mΩ (High side) and 75mΩ (Low side)
- High Efficiency
  Up to 96% Efficiency @ 5V Input, 3.3V Output
  Up to 94% efficiency @ 12V Input, 3.3V Output
- Wide Input Voltage Range: 4.75V to 18V @ 3.0-A loading
- Wide Output Voltage Range: 0.923V to 14V @ 3.0-A loading (54Watt output @max)
- Low Output Ripple and Allows Ceramic Output Capacitor
- Thermal Shutdown Protection
- 340-KHz Switching Frequency(fsw)
- Cycle By Cycle Over Current Limit
- +/-1.5% High Accuracy Feedback Voltage

Applications

- Wide Range of Applications for Low Voltage System
- Digital TV Power Supply
- High Definition Blu-ray Disc Players
- Networking Home Terminal
- Digital STB
- Ideal for Portable Applications

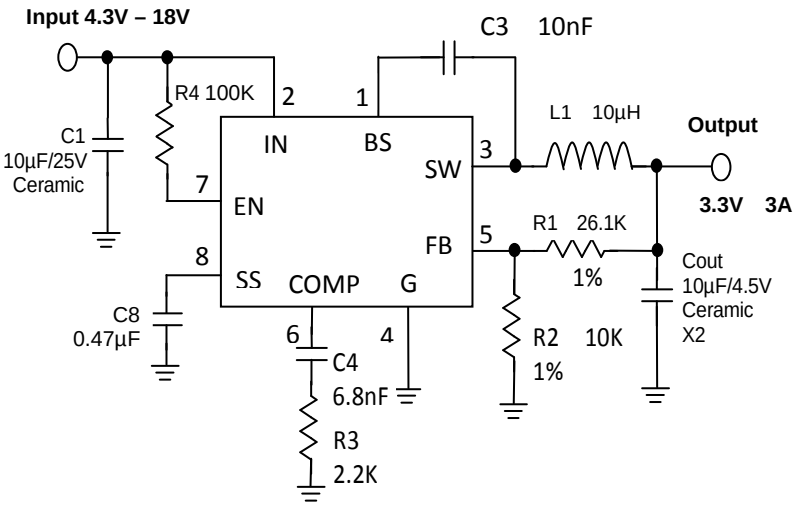
Descriptions

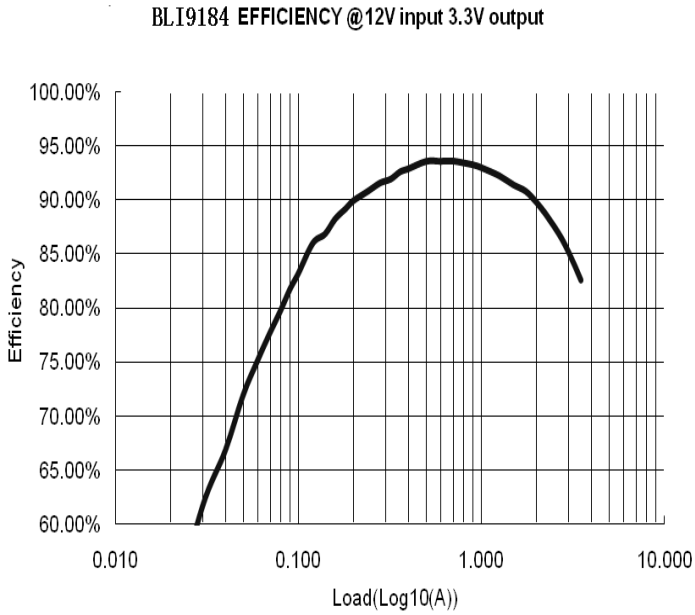
The BLI9184 is a current mode synchronous buck converter, and has a proprietary W-mode™® Gm curvature circuit that enables fast transient response, enables the device to adopt to both low ESR output capacitors, such as POSCAP or SP-CAP, and ultra-low ESR ceramic capacitors.

The BLI9184 operates from 4.75-V to 18-V Vin input, and the output voltage can be programmed between 0.923V to 14v with 3.0A output current, and +/-1.5% high accuracy output voltage.

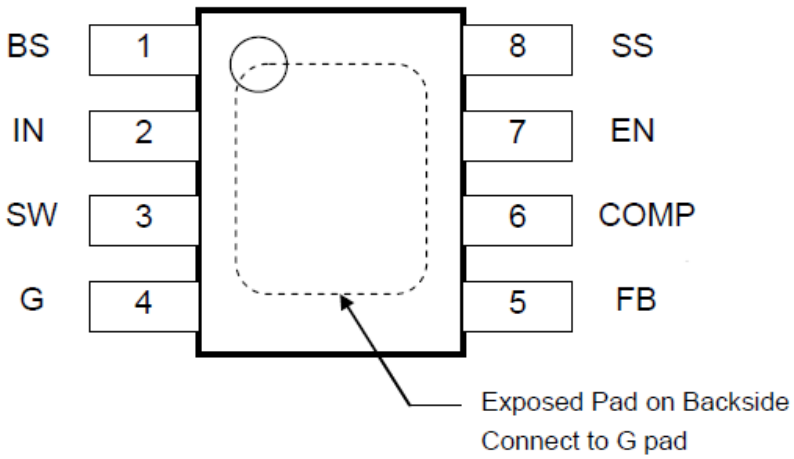
Due to 85mΩ (High side) and 75mΩ (Low side) integrated FETs, the BLI9184 works in high efficiency (up to 94% @12V Input, 3.3V output) .

Typical Application





PIN ARRANGEMENT



PIN FUNCTIONS

PIN		Description
NAME	NO.	Details
BS	1	Supply input for high-side NFET gate driver (boost terminal). Connect capacitor from this pin to SW pin. An internal PN diode is connected between VREG to BS pin.
IN	2	Power input and connected to high side NFET drain
SW	3	Switch node connection between high-side NFET and low-side NFET. Also serve as inputs to current comparators.
G	4	Signal ground pin, also serve as ground returns for low-side NFET.
FB	5	Converter feedback input. Connect with feedback resistor divider.
COMP	6	Compensation Node. Used to compensate control loop. Connect a series RC network from COMP to G. In some cases, an additional capacitor is required
EN	7	Enable control input
SS	8	Soft-start control. A external capacitor should be connected to G.

ABOSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise noted)

ITEMS	NAME	VALUE	UNIT
Voltage Range	IN	-0.3 to 20	V
	BS	-0.3 to 25	V
	SW	-2 to 20	V
	SW (10 ns transient)	-2.5 to 21	V
	FB,SS,COMP	-0.3 to 5.5	V
	EN	-0.3 to 8	V
TJ	Operation Junction	-40 to +150	℃
Tstg	Storage temperature	-55 to +150	℃

ELECTRICAL CHARACTERISTICS

Over operating free-air temperature range(unless otherwise noted)

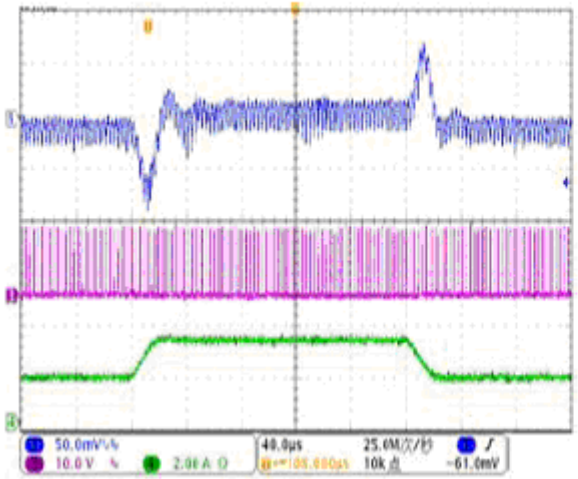
VIN=12V, TA=25℃

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Current						
Iin	Operating-non-switching supply current	VIN current, TA=25℃, EN=1.8V, VFB=1.0V		1.3	2.0	mA
ISDN	Shut Down Supply Current	VEN=0V		2	4	μA
VFB	Feedback Voltage	4.3V ≤VIN≤18V	0.900	0.925	0.95	V
OVP	Feedback Overvoltage Threshold			1.1		V
Aea	Error Amplifier Voltage Gain			1000		V/V
Gea	Error Amplifier Transconductance	△IC=+/-10μA		900		μA/V
RDS(on)_1	High Side Switch ON Resistance			85		mΩ
RDS(on)_2	Low Side Switch ON Resistance			75		mΩ
Ileakgae	High Side Switch Leakage Current	VEN=0V, VSW=0V			10	μA
ILM_H	High Side Switch Current Limit	Minimum Duty Cycle	3.8	4.5		A
ILM_L	Low Side Switch Current Limit	From Drain to Source		1.0		A
Gcs	COMP Voltage to Current Sense Transconductance			3.5		A/V
Fsw_1	Switching Frequency			340		KHz
Fsw_2	Short Circuit Switching Frequency	VFB=0V		100		KHz
Dmax	Maximum Duty Cycle	VFB=1.0V		90		%
TON_min	Minimum ON Time			220		ns
VEN_1	EN Threshold Voltage	VEN Rising	1.1	1.5	2.0	V
VHys_1	EN Threshold voltage's Hysteresis			100		mV
VEN_2	EN Lockout Threshold Voltage		1.8	2.0	2.2	V
VHys_2	EN Lockout Hysteresis			210		mV
VUVLO	Input Under Voltage Lockout Threshold	VIN Rising	3.0	3.6	4.2	V
VHys_3	Input Under Voltage Lockout Threshold Hysteresis			600		mV
Iss	Soft-Start Current	Vss=0V	4.25	4.40	4.55	μA
Tss	Soft-Start Period	Css=0.1μF		14		ms
TSD	Thermal Shutdown			160		℃

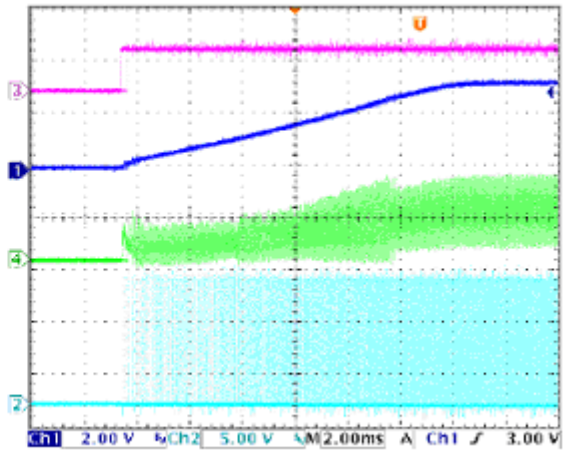
TYPICAL PERFORMANCE CHARACTERISTICS

Vin=12V,Vout=1.2V, L=2.2μH, Cin=10μF, Cout=2X22μF, TA=+25℃

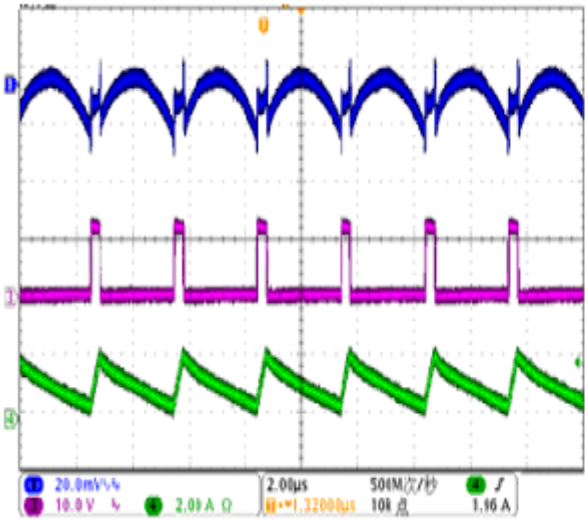
Fast Transient Response (1.5A → 3.0A, 1.2V)



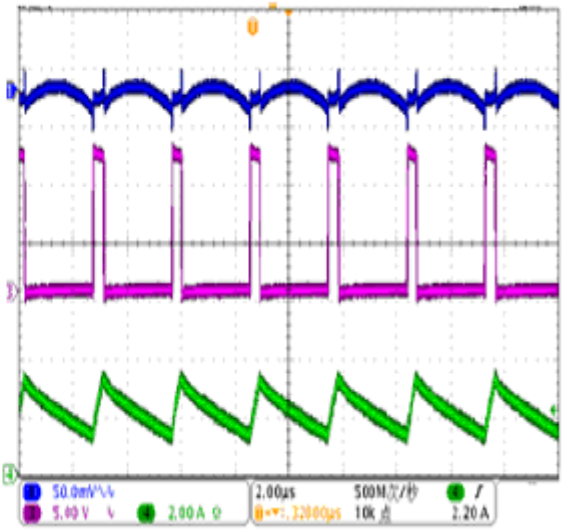
Startup through Enable(Vout=3.3V)



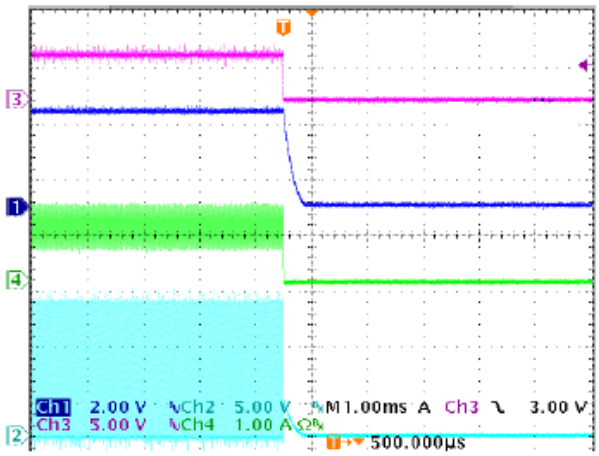
1.2V 1A Load Operation



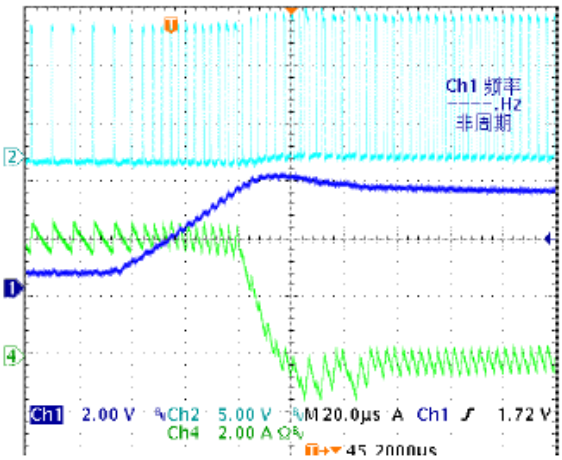
1.2V 2A Load Operation



Shutdown through Enable (Vout=3.3V)



Short Circuit Recovery (Vout=3.3V)



APPLICATION SCHEMATIC (1)

1) With Electrolytic Capacitor

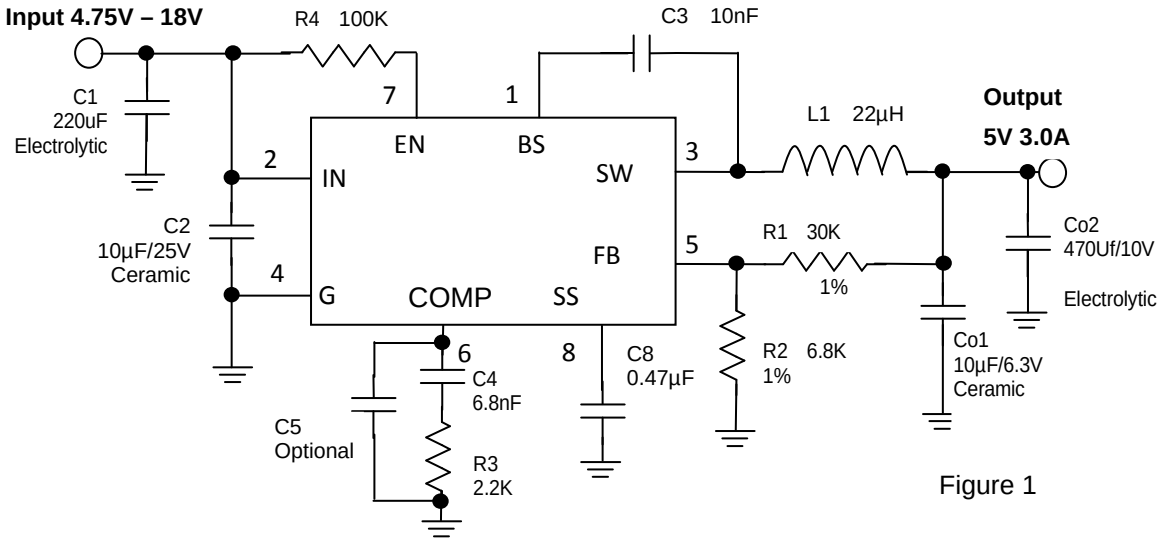


Figure 1

Compatible with main competitors without any external component change!

RECOMMENDED COMPONENT SELECTION

Vout	Cout	R1	R2	R3 (comp)	C4 (comp)	C5 (optional)	L(inductor)
1.0V	470µF/6.3V/Electrolytic	1.0K	10K	50 Ω	10nF	100pF	3.3µH
1.2V	470µF/6.3V/Electrolytic	4.7K	15K	100 Ω	10nF	100pF	3.3µH
1.8V	470µF/6.3V/Electrolytic	9.7K	10K	300 Ω	6.8nF	100pF	4.7µH
2.5V	470µF/6.3V/Electrolytic	12.0K	6.8K	1.5K Ω	6.8nF	100pF	6.8µH
3.3V	470µF/6.3V/Electrolytic	26.1K	10K	2.2K Ω	6.8nF	100pF	10µH
5.0V	470µF/10V/Electrolytic	30.0K	6.8K	2.7K Ω	6.8nF	100pF	22µH
12V	470µF/25V/Electrolytic	62.0K	5.1K	3.3K Ω	6.8nF	100pF	47µH

APPLICATION SCHEMATIC (2)

2) Fast Transient Response Without Electrolytic Capacitor

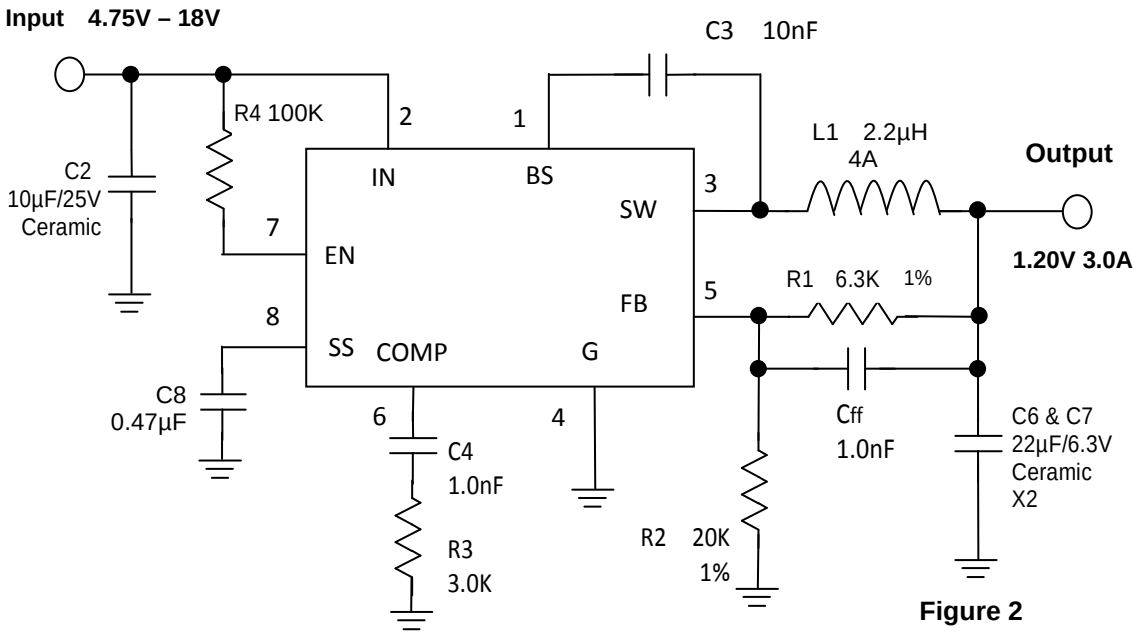


Figure 2

RECOMMENDED COMPONENT SELECTION

Vout	Cout	R1	R2	R3 (comp)	C4 (comp)	Cff	L inductor)
1.0V	22µF Ceramic X2	2.0K	20K	3.0K Ω	1.0nF	2.2nF	2.2µH
1.2V	22µF Ceramic X2	6.3K	20K	3.0K Ω	1.0nF	1.0nF	2.2µH
1.8V	22µF Ceramic X2	19.4K	20K	3.0K Ω	1.0nF	680pF	3.3µH
2.5V	22µF Ceramic X2	34.5K	20K	3.0K Ω	1.0nF	680pF	4.7µH
3.3V	22µF Ceramic X2	52.2K	20K	3.0K Ω	1.0nF	680pF	6.8µH
5.0V	22µF Ceramic X2	89.5K	20K	3.0K Ω	1.0nF	390pF	22µH
1.0V	47µF SP Cap	2.0K	20K	3.0K Ω	1.0nF	2.2nF	2.2µH
1.2V	47µF SP Cap	6.3K	20K	3.0K Ω	1.0nF	1.0nF	2.2µH
1.8V	47µF SP Cap	19.4K	20K	3.0K Ω	1.0nF	680pF	3.3µH
2.5V	47µF SP Cap	34.5K	20K	3.0K Ω	1.0nF	680pF	4.7µH
3.3V	47µF SP Cap	52.2K	20K	3.0K Ω	1.0nF	680pF	6.8µH
5.0V	47µF SP Cap	89.5K	20K	3.0K Ω	1.0nF	390pF	22µH

APPLICATION NOTES

a) C2 ceramic 电容尽量靠近芯片的 PIN2 和 PIN4 放置;

b) 若使用电解电容做输入电容，C2 必须加入，且须用 100nF 或 1μF 瓷片电容。此电容容值越大越好。

c) 使用 47μH 电感时，由于每次 switching 传输的能量大，输出需要更大的电容，以使大信号的反馈环路稳定。使用 47μH 电感时，输出须用大于或等于 330μF 的电解电容作能量 Bulk。

d) 大电流路径尽量短，且尽量与芯片在同一 PCB 层次。避免大电流路径打过孔跨层连接。

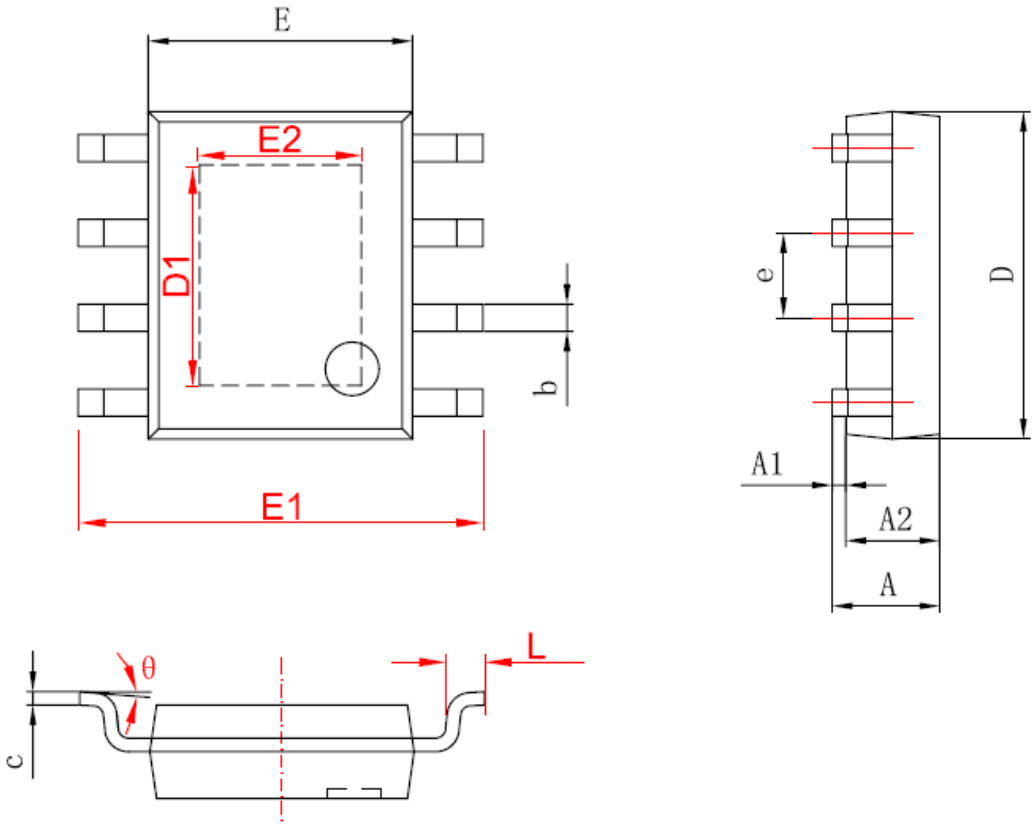
e) 若成本可行，在高效率设计中，应尽量使用瓷片电容或较小 ESR（如：30mohm）的电解电容，效率可有效提升 1%.

f) EN 脚（第 7 脚）上拉电阻要求不低于 100K 欧。

g) 若多个芯片共享同一输入电容,需调节第 8 脚软起动电容的电容值分时延迟启动各芯片,以规避多个芯片同时启动对电源输入电容产生冲击。延迟时间：每 100nF 电容延迟 15ms。

PACKAGE INFORMATION

Package	SOP8	Devices per Tube	100	Unit	mm
		Devices per reel	2500		



字符	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.050	0.150	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
D1	3.202	3.402	0.126	0.134
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
E2	2.313	2.513	0.091	0.099
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°